

Future Power Delivery System

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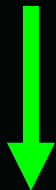
NC State University

July 22, 2008

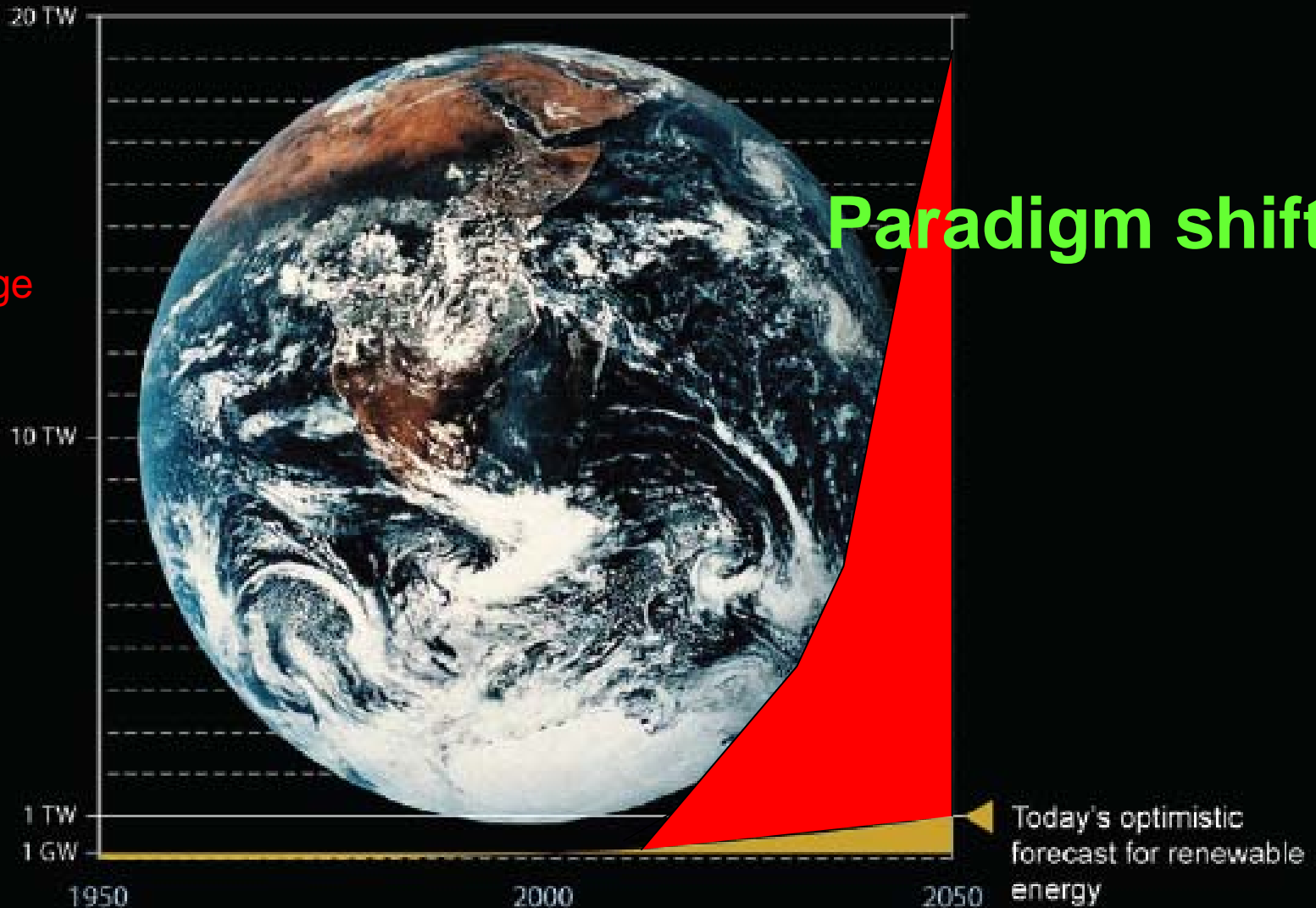


Magnitude of Challenge Requires Global Action and a Change in Trajectory

- Energy Crisis**
- Security
 - Sustainability
 - Climate Change



Green and renewable energy



A Paradigm Shift like the Computer Industry

Pre-1980s



Centralized Mainframes

Paradigm Shift



Distributed Computing

- Shipping 250M pcs/yr.
- Ubiquitous ownership
- Ubiquitous use
- Ubiquitous sharing

Paradigm Shift for the Power Industry

Today



Centralized Generation
100+ year old technology

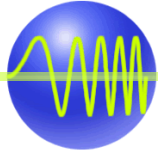
Paradigm Shift

Future
Power
System



Distributed Renewable
Energy Resources (DRER)

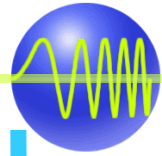
- Ubiquitous sales
- Ubiquitous ownership
- Ubiquitous use
- Ubiquitous sharing



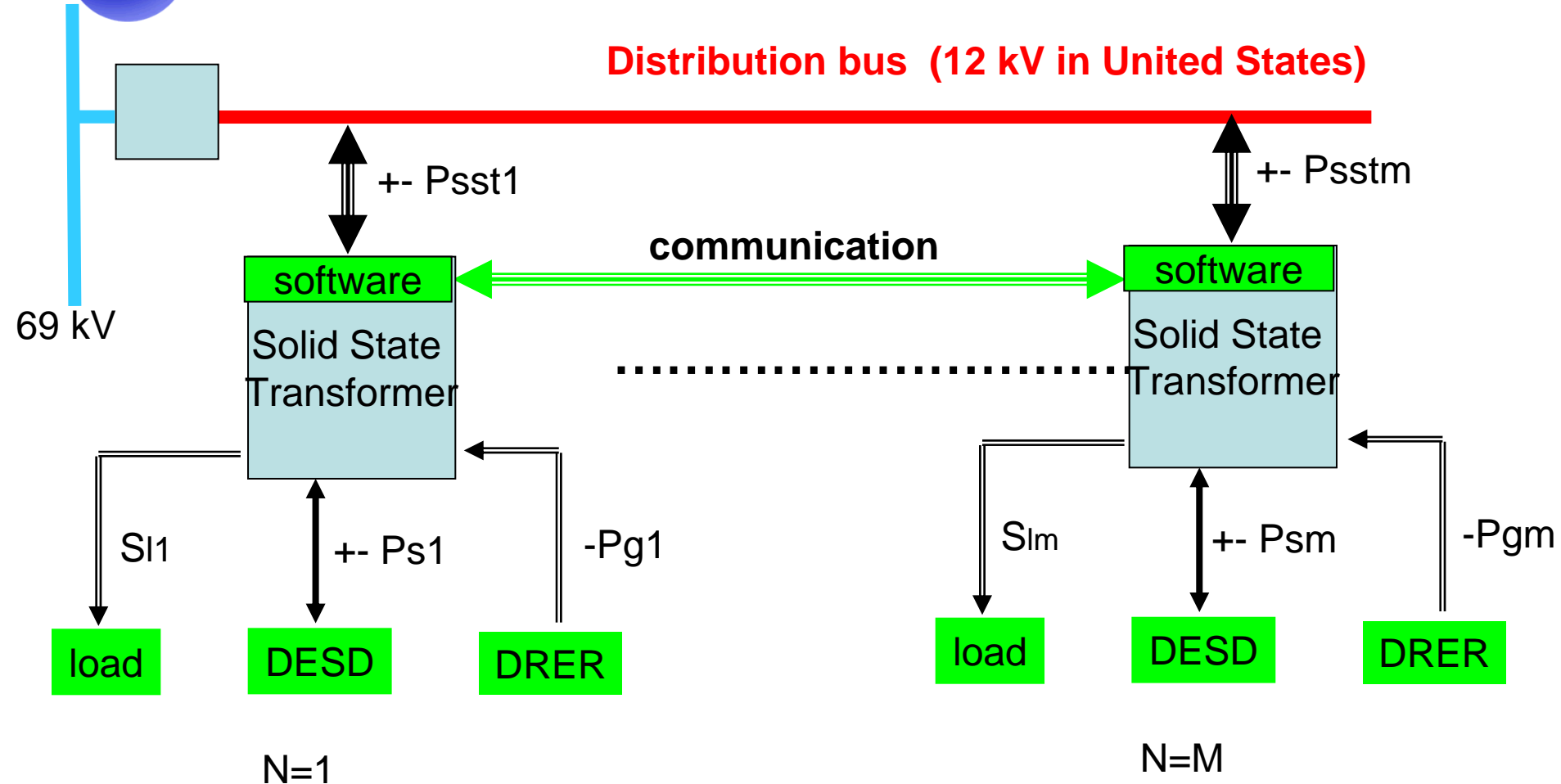
Future Delivery System

- **A new delivery system to allow:**
 - Plug-and-play of any Distributed Renewable Energy Resource (DRER) anywhere and anytime.
 - Plug-and-play of any Distributed Energy Storage Device (DESD) anywhere and anytime.

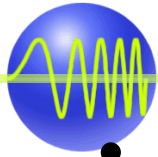
- **A new management system for DRER, DESD and load**
 - Control is distributed
 - everything is connected by communication



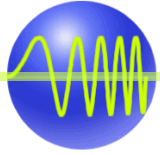
Future Distribution System



- Need to isolate low voltage side plug & play action from the bus
- Low voltage side voltage = 120V, 480 V etc
- SST rating: 10 kVA, 100 kVA and 1000 kVA



- Allows plug & play
 - System immediately recognize the load, storage and generation (*real time SI, Ps, Pg*)
- Power factor correction
 - Unity power factor on the distribution bus ($Q_{bus}=0$)
- Instant Demand side management
 - Adjust load bus voltage (*VI adjustable*)
- Limit fault current
 - SST limits current at 2 p.u.
- IEC16850 Standard on Grid Side
- IEEE 1547 on the load/DRER/DESD side
- Real time information of the system
 - Serve as advanced metering
- Optimal operation by distributed software
 - Electric constraints
 - Economic constraints
 - Social constraints



Control Objectives

At any given $t=t_k$,

$$P_{total}(t_k) = \text{sum}(P_{sst1}(t_k), \dots, P_{sstm}(t_k))$$

Under constraints $A(t_k)$, $B(t_k)$, $C(t_k)$

Objective: maximize $P_{g1} \dots m$

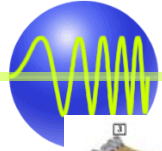
or

Objective: Minimize P_{total}

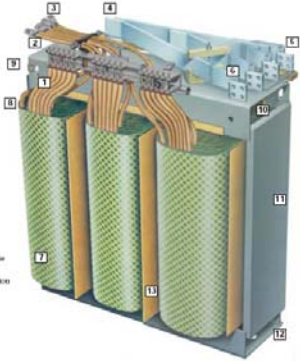
or

Objective: keep $P_{total} = \text{constant}$

.....



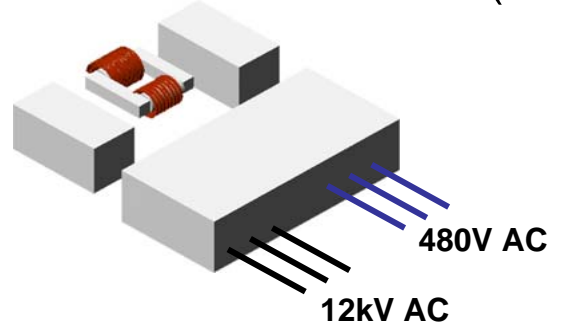
Enabling Technology



Conventional Transformer

size reduction
weight reduction

Solid State Transformer (SST)

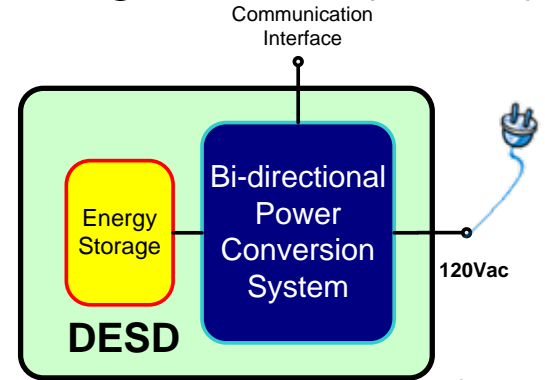


Today's High Power
Li-ion battery



reduction in size, cost,
weight

Distributed Energy
Storage Device (DESD)



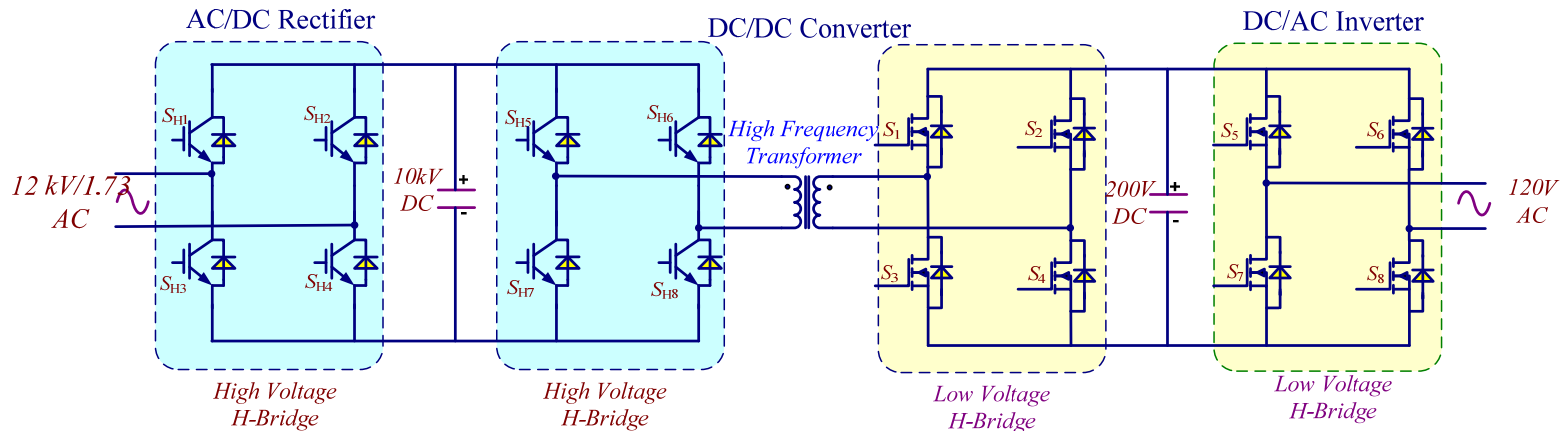
Example 10 kVA SST

for single-phase residential applications

Input side: 15kV, 2A SiC IGBTs

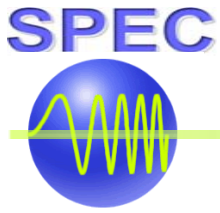
Output side: 300V, 100A GaN FETs

High voltage DC bus: 10kV, low voltage DC bus: 200V.



Major issues:

- Control power self-generation
- Insulation
- Thermal management
- Control
- Communication Interface
- Interface to load, DESD and DRER



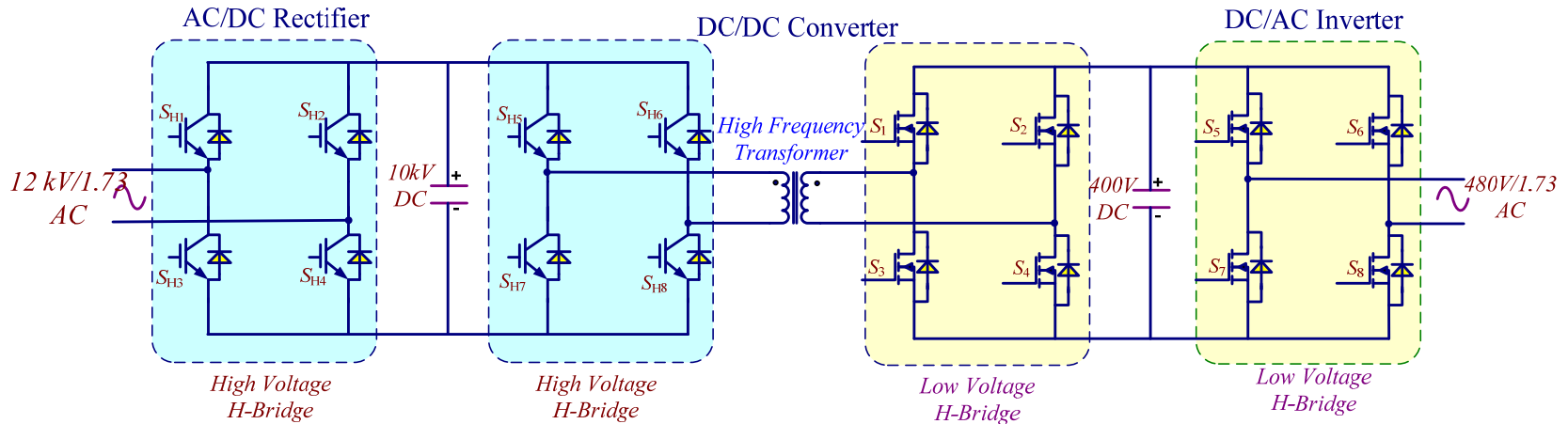
Example 100 kVA SST

for 3-phase industrial applications

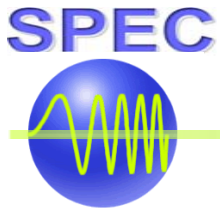
Input side: 15kV, 5 A SiC IGBT

Output side: 600V, 120A GaN devices

High voltage DC bus: 10kV, low voltage DC bus: 400V



(1 phase shown)



Example High Voltage SST

SST Topology

Modular Converter Structure
(one phase shown)

Input: 69 kV

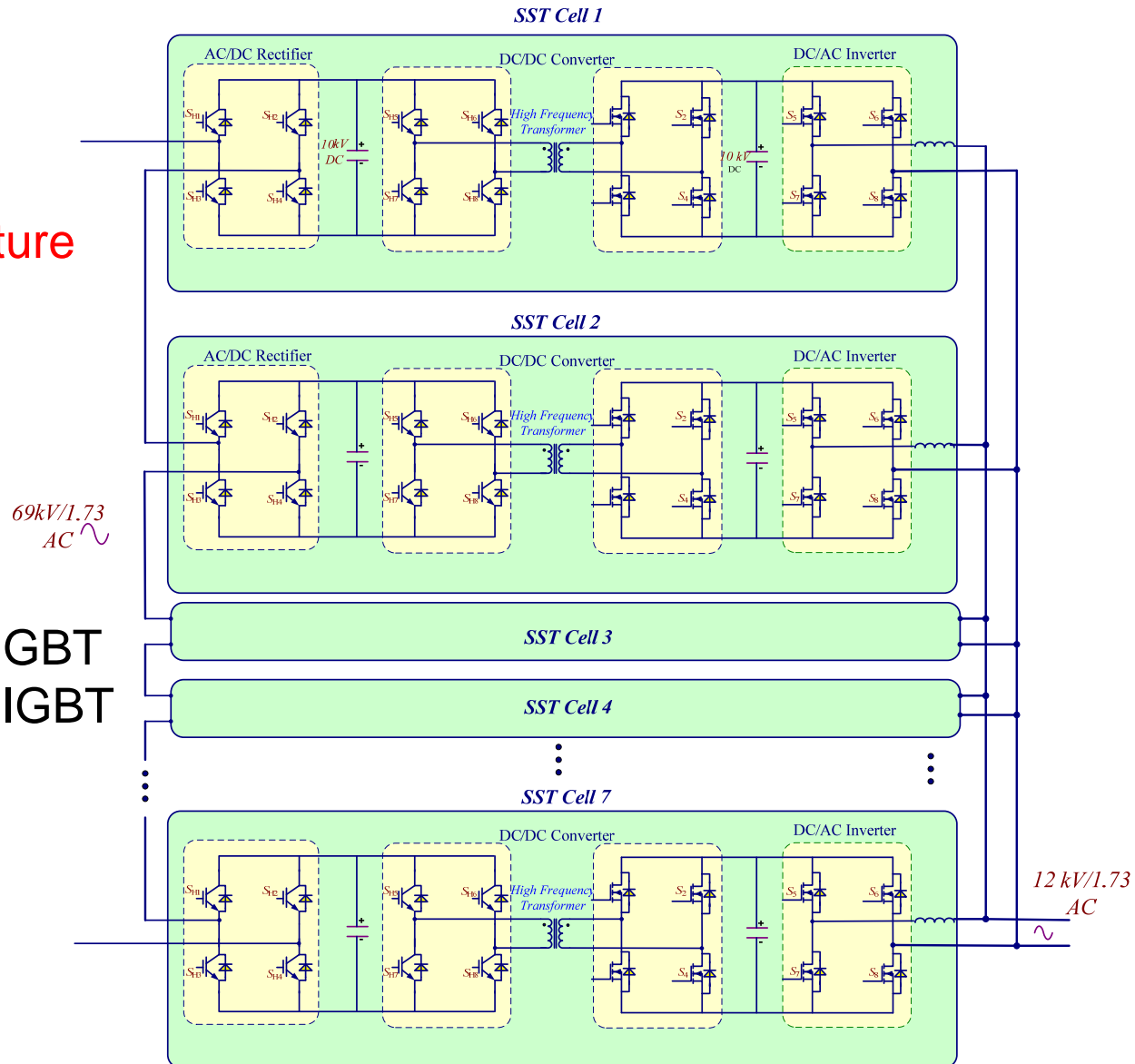
Output: 12 kV

Rating: 700 kVA

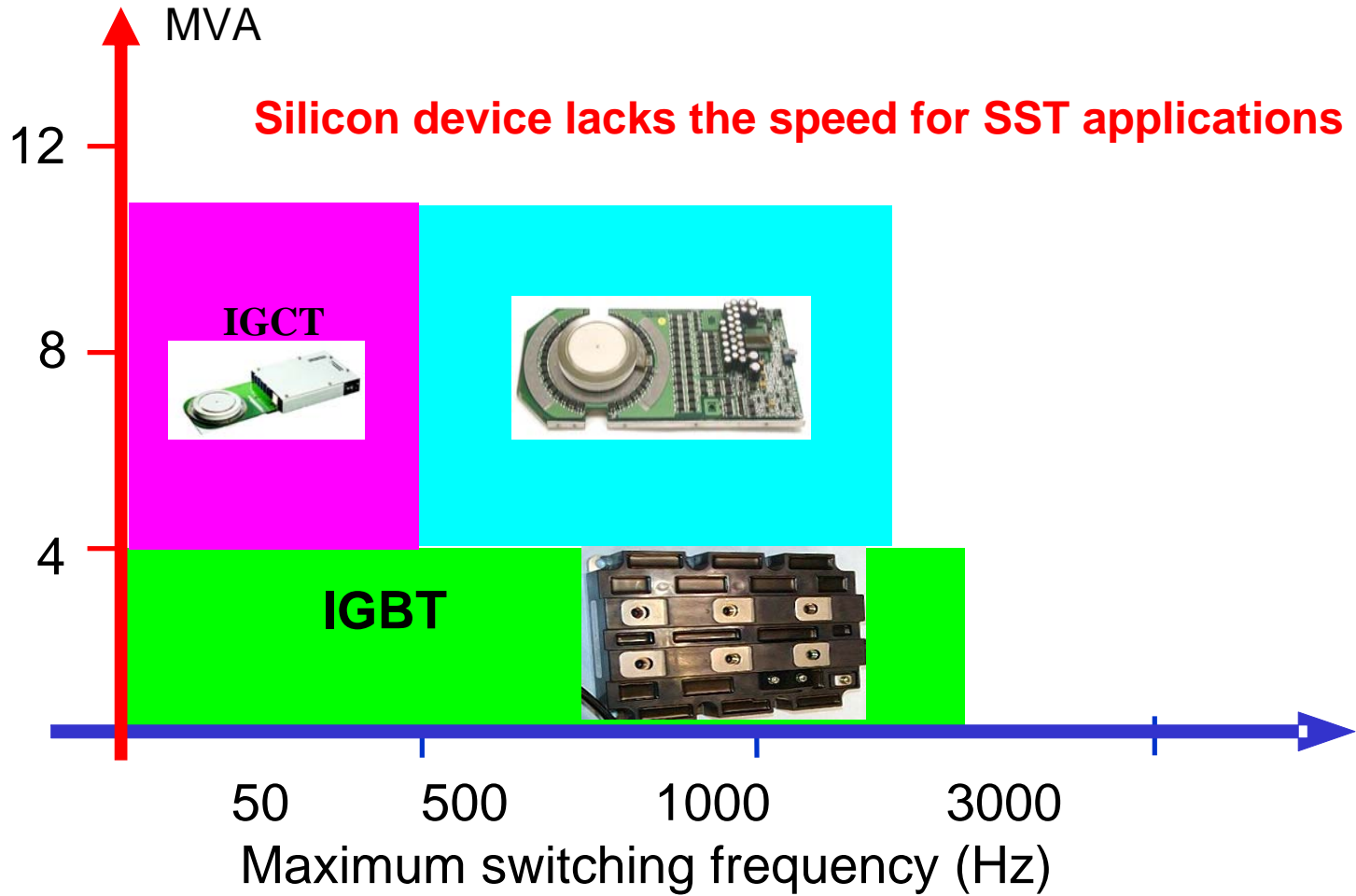
Devices:

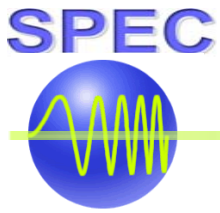
Input side: 15 kV/5 A SiC IGBT

Output side: 15 kV/5A SiC IGBT

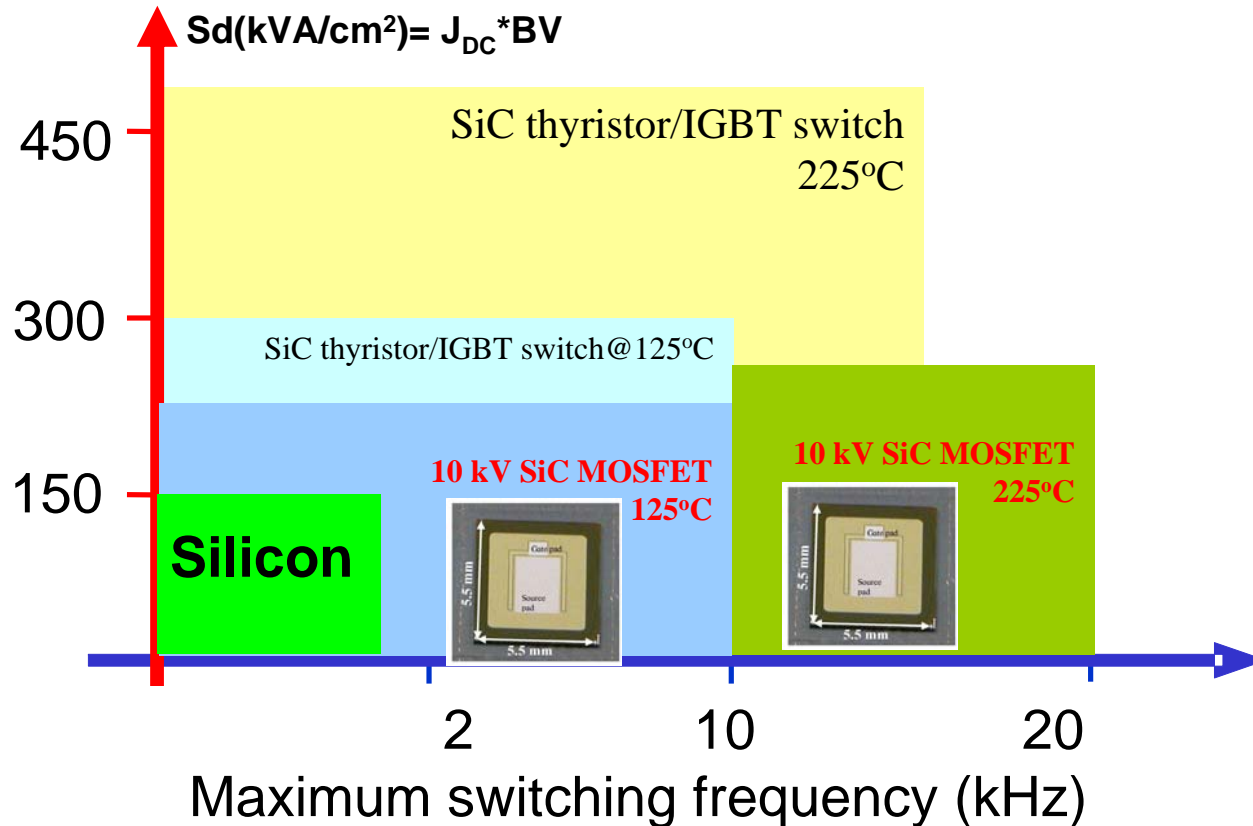


State-of-the-art silicon power device



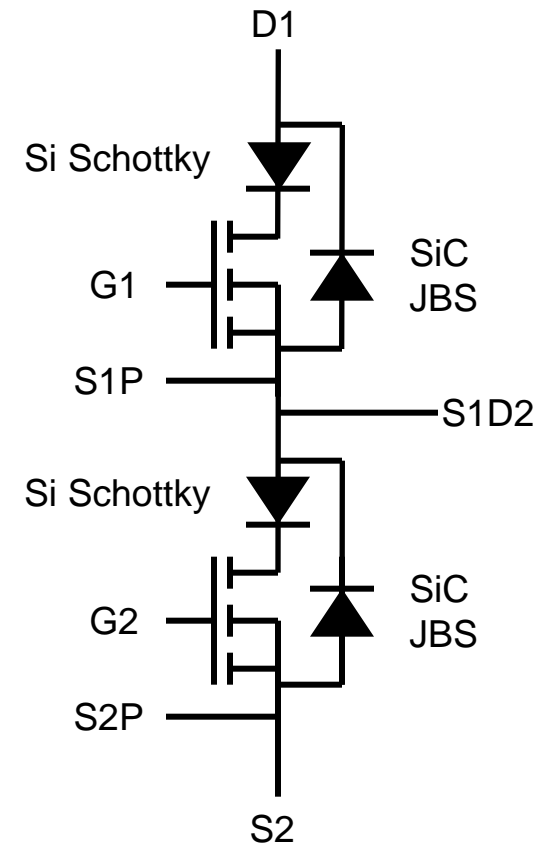
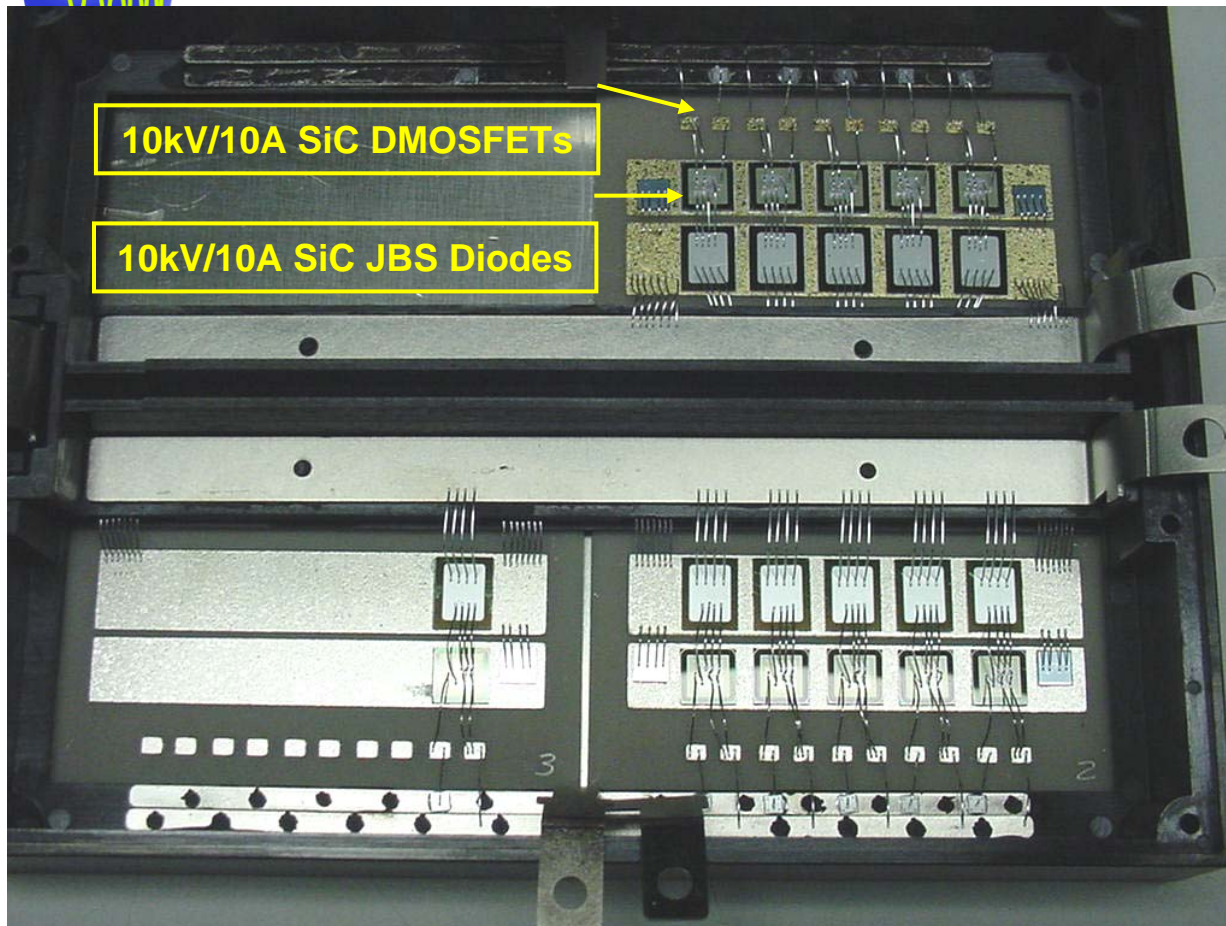
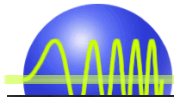


Silicon Carbide Power Device



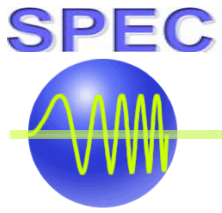
- SiC material can potentially improve the frequency-power rating trade off by 15 times

lower losses and higher operating temperature allows the increase of P and f



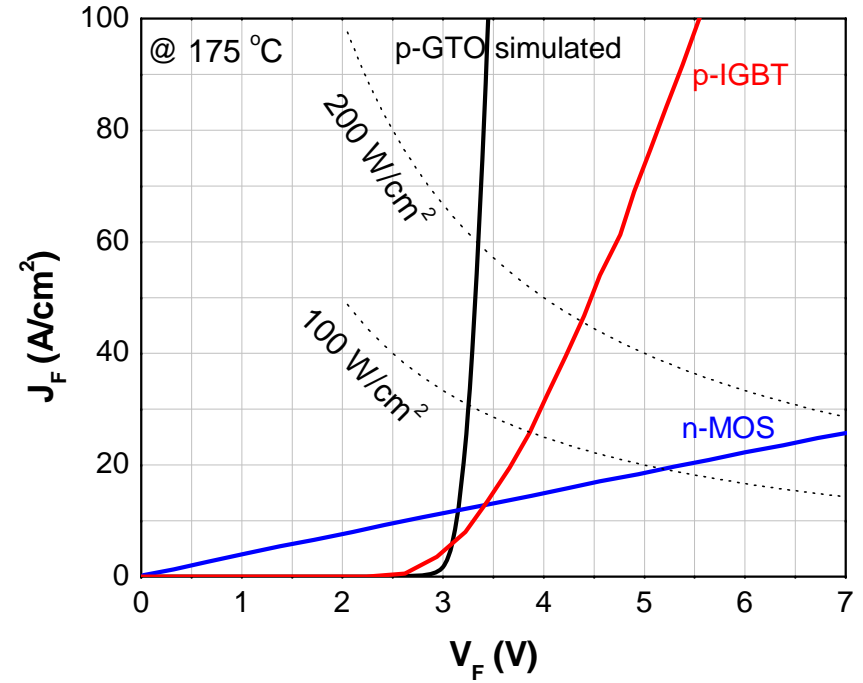
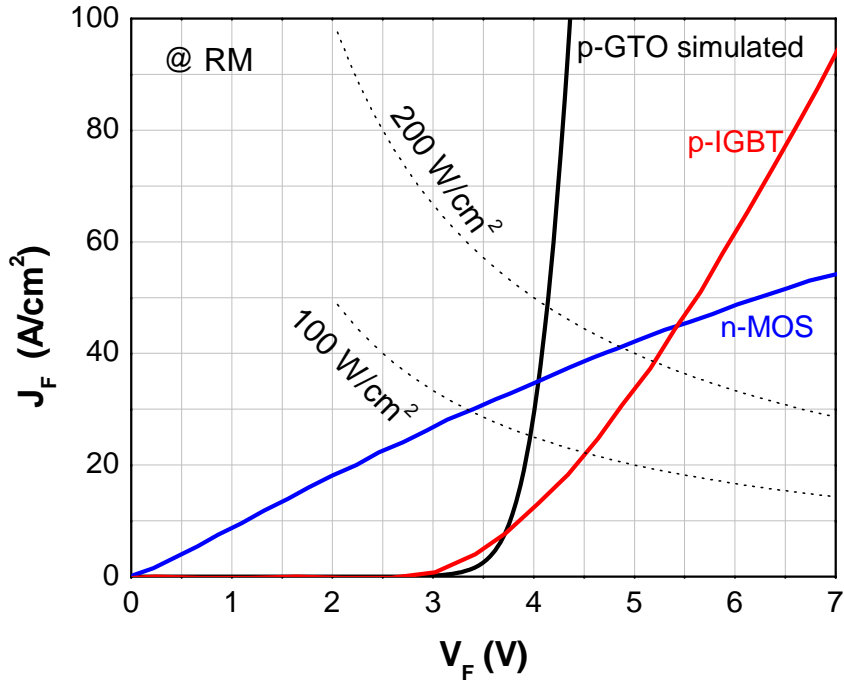
- High current requires multiple chips in parallel, a challenge for SiC
- Lower current application such as 10 kVA SST makes sense for initial insertion

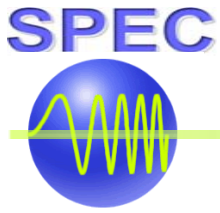
Questions?



SiC Bipolar Devices

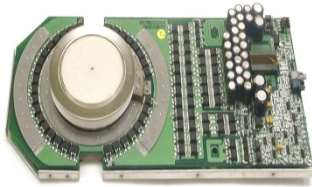
BV = 10,000 V





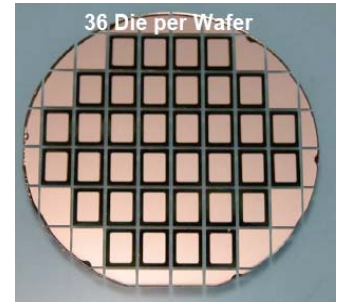
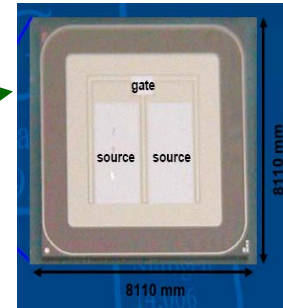
Fundamental Science

4.5 kV, 125°C, 150 kW/cm²
Silicon Bipolar Technology



*15 X improvement in speed*power*

15 kV, 200°C, 350 kW/cm²
Silicon Carbide IGBT Technology
and 600V, 100A GaN Technology

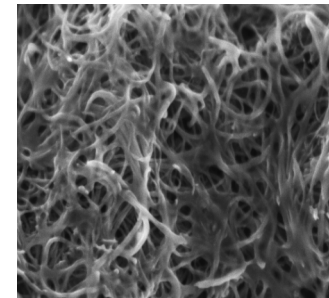


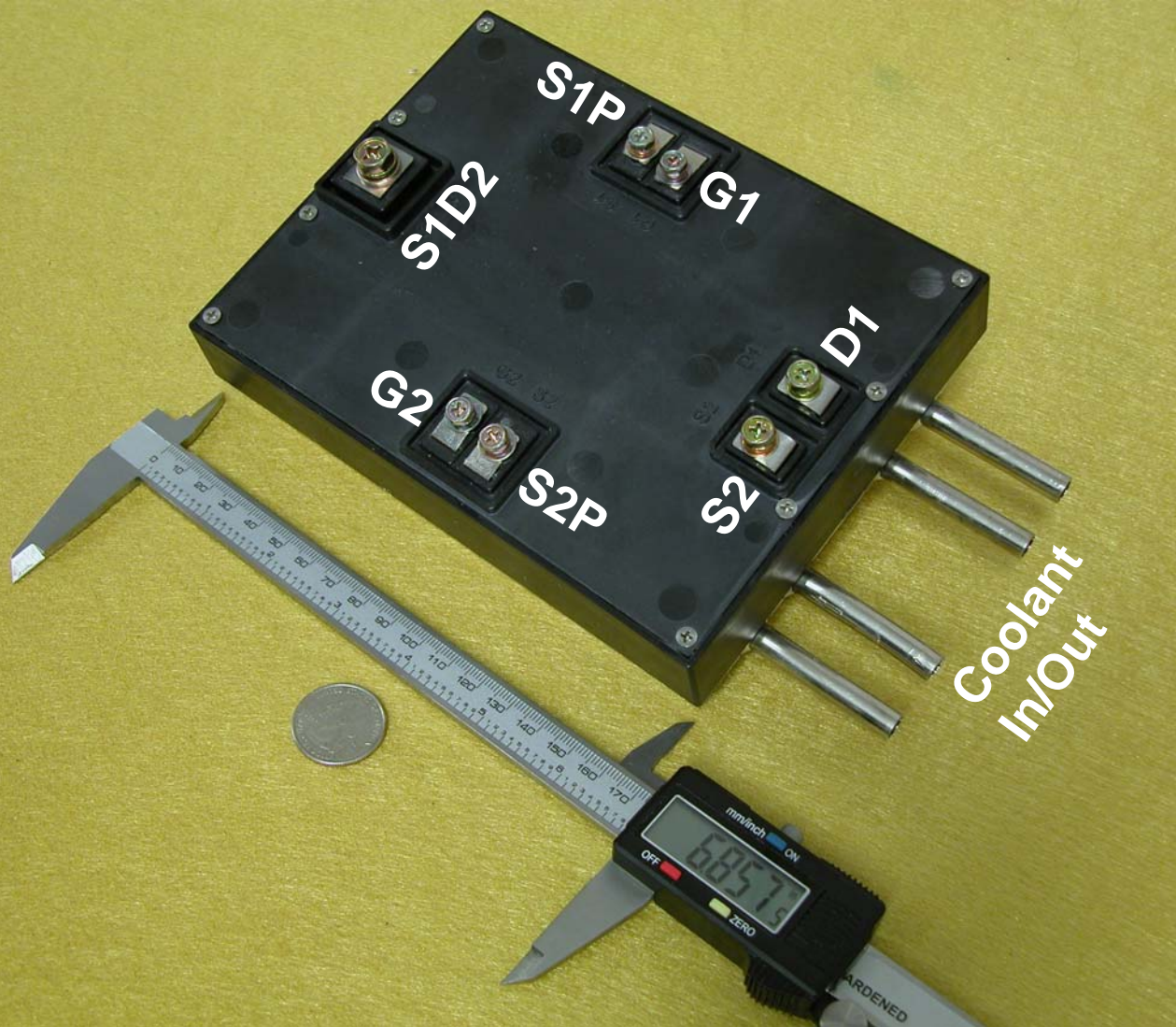
Today's Advanced
Li-ion Cell



3 X improvement in Li-ion power density

Nanofiber Li-ion Cell
(250WH/kg, 3.5 kW/kg, 20000 cycle)





Dimensions ~ 7 x 5 inches

